

Oleg Evgenevich Tereshchenko

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#	Paper	IF	Citations
166	Plasma-Wave Terahertz Detection Mediated by Topological Insulators Surface States. <i>Nano Letters</i> , 2016 , 16, 80-7	11.5	99
165	Formation of Inert Bi ₂ Se ₃ (0001) Cleaved Surface. <i>Crystal Growth and Design</i> , 2011 , 11, 5507-5514	3.5	97
164	Oxygen deficiency defects in amorphous Al ₂ O ₃ . <i>Journal of Applied Physics</i> , 2010 , 108, 013501	2.5	88
163	Composition and structure of HCl-isopropanol treated and vacuum annealed GaAs(100) surfaces. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1999 , 17, 2655-2662	2.9	86
162	Subcycle observation of lightwave-driven Dirac currents in a topological surface band. <i>Nature</i> , 2018 , 562, 396-400	50.4	83
161	Topological surface states with persistent high spin polarization across the Dirac point in Bi ₂ Te ₂ Se and Bi ₂ Se ₂ Te. <i>Physical Review Letters</i> , 2012 , 109, 166802	7.4	77
160	Vibrations in binary and ternary topological insulators: First-principles calculations and Raman spectroscopy measurements. <i>Physical Review B</i> , 2012 , 86,	3.3	68
159	Snapshots of Dirac fermions near the Dirac point in topological insulators. <i>Nano Letters</i> , 2013 , 13, 5797-8025	8.25	62
158	Dual nature of magnetic dopants and competing trends in topological insulators. <i>Nature Communications</i> , 2016 , 7, 12027	17.4	61
157	Surface passivation and morphology of GaAs(1 0 0) treated in HCl-isopropanol solution. <i>Applied Surface Science</i> , 2004 , 235, 249-259	6.7	61
156	Signatures of Dirac fermion-mediated magnetic order. <i>Nature Communications</i> , 2014 , 5, 5349	17.4	60
155	Unoccupied topological states on bismuth chalcogenides. <i>Physical Review B</i> , 2012 , 86,	3.3	54
154	Inertness and degradation of (0001) surface of Bi ₂ Se ₃ topological insulator. <i>Journal of Applied Physics</i> , 2012 , 112, 113702	2.5	53
153	Spin-texture inversion in the giant Rashba semiconductor BiTeI. <i>Nature Communications</i> , 2016 , 7, 11621	17.4	52
152	Bulk and surface Rashba splitting in single termination BiTeCl. <i>New Journal of Physics</i> , 2013 , 15, 085022	2.9	50
151	Melt growth of bulk Bi ₂ Te ₃ crystals with a natural p-n junction. <i>CrystEngComm</i> , 2014 , 16, 581-584	3.3	43
150	Preparation of clean reconstructed InAs(001) surfaces using HCl/isopropanol wet treatments. <i>Applied Physics Letters</i> , 2003 , 82, 4280-4282	3.4	42

149	Tuning the Dirac point position in Bi(2)Se(3)(0001) via surface carbon doping. <i>Physical Review Letters</i> , 2014 , 113, 116802	7.4	40
148	Visualizing spin-dependent bulk scattering and breakdown of the linear dispersion relation in Bi ₂ Te ₃ . <i>Physical Review B</i> , 2013 , 88,	3.3	33
147	Experimental Realization of a Topological p-n Junction by Intrinsic Defect Grading. <i>Advanced Materials</i> , 2016 , 28, 2183-8	24	33
146	Systematics of electronic and magnetic properties in the transition metal doped Sb ₂ Te ₃ quantum anomalous Hall platform. <i>Physical Review B</i> , 2018 , 97,	3.3	32
145	Electronic and spin structure of the topological insulator Bi ₂ Te _{2.4} Se _{0.6} . <i>Physical Review B</i> , 2014 , 89,	3.3	32
144	Low-temperature method of cleaning p-GaN(0001) surfaces for photoemitters with effective negative electron affinity. <i>Physics of the Solid State</i> , 2004 , 46, 1949-1953	0.8	32
143	Systematics of molecular self-assembled networks at topological insulators surfaces. <i>Nano Letters</i> , 2015 , 15, 2442-7	11.5	31
142	Lattice dynamics of bismuth tellurohalides. <i>Physical Review B</i> , 2012 , 86,	3.3	31
141	Probing the electronic properties of individual MnPc molecules coupled to topological states. <i>Nano Letters</i> , 2014 , 14, 5092-6	11.5	30
140	Atomic structure and electronic properties of HCl/isopropanol treated and vacuum annealed GaAs(100) surface. <i>Applied Surface Science</i> , 1999 , 142, 75-80	6.7	30
139	Ultrafast energy- and momentum-resolved surface Dirac photocurrents in the topological insulator Sb ₂ Te ₃ . <i>Physical Review B</i> , 2017 , 95,	3.3	25
138	Soft nitridation of GaAs(100) by hydrazine sulfide solutions: Effect on surface recombination and surface barrier. <i>Applied Physics Letters</i> , 2007 , 90, 022104	3.4	25
137	Cesium-induced surface conversion: From As-rich to Ga-rich GaAs(001) at reduced temperatures. <i>Physical Review B</i> , 2005 , 71,	3.3	21
136	Defect and structural imperfection effects on the electronic properties of BiTeI surfaces. <i>New Journal of Physics</i> , 2014 , 16, 075013	2.9	20
135	Electron dynamics of unoccupied states in topological insulators. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 2014 , 195, 258-262	1.7	20
134	Decrease in the bond energy of arsenic atoms on the GaAs(100)-(2 \times 2)/c(2 \times 2) surface due to the effect of adsorbed cesium. <i>JETP Letters</i> , 2004 , 79, 131-135	1.2	20
133	Unoccupied topological surface state in Bi ₂ Te ₂ Se. <i>Physical Review B</i> , 2013 , 88,	3.3	19
132	Termination-dependent surface properties in the giant-Rashba semiconductors BiTeX (X=Cl, Br, I). <i>Physical Review B</i> , 2015 , 92,	3.3	19

131	Structure and composition of chemically prepared and vacuum annealed InSb(001) surfaces. <i>Applied Surface Science</i> , 2006 , 252, 7684-7690	6.7	19
130	Structural and electronic transformations at the Cs/GaAs(100) interface. <i>Surface Science</i> , 2002 , 507-510, 51-56	1.8	19
129	Tunable non-integer high-harmonic generation in a topological insulator. <i>Nature</i> , 2021 , 593, 385-390	50.4	19
128	Prolonged duration of nonequibrated Dirac fermions in neutral topological insulators. <i>Scientific Reports</i> , 2017 , 7, 14080	4.9	18
127	Chemically prepared well-ordered InP(0 0 1) surfaces. <i>Surface Science</i> , 2006 , 600, 3160-3166	1.8	18
126	Crystal growth of Bi ₂ Te ₃ and noble cleaved (0001) surface properties. <i>Journal of Solid State Chemistry</i> , 2016 , 236, 203-208	3.3	17
125	Dynamics of the BiTeI lattice at high pressures. <i>JETP Letters</i> , 2014 , 98, 557-561	1.2	17
124	Dirac gap opening and Dirac-fermion-mediated magnetic coupling in antiferromagnetic Gd-doped topological insulators and their manipulation by synchrotron radiation. <i>Scientific Reports</i> , 2019 , 9, 4813	4.9	16
123	Well-ordered (1 0 0) InAs surfaces using wet chemical treatments. <i>Surface Science</i> , 2004 , 570, 237-244	1.8	16
122	Chemistry of Wet Treatment of GaAs(111)B and GaAs(111)A in Hydrazine-Sulfide Solutions. <i>Journal of the Electrochemical Society</i> , 2011 , 158, D127	3.9	15
121	Stability of the (0001) surface of the Bi ₂ Se ₃ topological insulator. <i>JETP Letters</i> , 2011 , 94, 465-468	1.2	15
120	Surface and bulk origin of the optical anisotropy of As-rich GaAs(001) and Ga _{1-x} In _x As(001). <i>Physical Review B</i> , 2003 , 67,	3.3	15
119	Local-order of chemically-prepared GaAs() surfaces. <i>Surface Science</i> , 2002 , 507-510, 411-416	1.8	15
118	Surface spin-polarized currents generated in topological insulators by circularly polarized synchrotron radiation and their photoelectron spectroscopy indication. <i>Physics of the Solid State</i> , 2016 , 58, 1675-1686	0.8	14
117	InAs-based metal-oxide-semiconductor structure formation in low-energy Townsend discharge. <i>Applied Physics Letters</i> , 2015 , 107, 173501	3.4	14
116	Clean reconstructed InAs(1 1 1) A and B surfaces using chemical treatments and annealing. <i>Surface Science</i> , 2009 , 603, 518-522	1.8	14
115	Energy distributions of photoelectrons emitted from p-GaN(Cs, O) with effective negative electron affinity. <i>JETP Letters</i> , 2004 , 79, 479-483	1.2	13
114	Signatures of in-plane and out-of-plane magnetization generated by synchrotron radiation in magnetically doped and pristine topological insulators. <i>Physical Review B</i> , 2018 , 97,	3.3	12

113	Oxide-free InAs(111)A interface in metal-oxide-semiconductor structure with very low density of states prepared by anodic oxidation. <i>Applied Physics Letters</i> , 2014 , 105, 161601	3.4	12
112	Optical detection of spin-filter effect for electron spin polarimetry. <i>Applied Physics Letters</i> , 2014 , 105, 052402	3.4	12
111	Out-of-plane polarization induced in magnetically-doped topological insulator Bi _{1.37} V _{0.03} Sb _{0.6} Te ₂ Se by circularly polarized synchrotron radiation above a Curie temperature. <i>Applied Physics Letters</i> , 2016 , 109, 222404	3.4	12
110	Electrically Controlled Spin Injection from Giant Rashba Spin-Orbit Conductor BiTeBr. <i>Nano Letters</i> , 2020 , 20, 4782-4791	11.5	11
109	Electronic and spin structure of the wide-band-gap topological insulator: Nearly stoichiometric Bi ₂ Te ₂ S. <i>Physical Review B</i> , 2018 , 97,	3.3	11
108	Giant Magnetic Band Gap in the Rashba-Split Surface State of Vanadium-Doped BiTeI: A Combined Photoemission and Ab Initio Study. <i>Scientific Reports</i> , 2017 , 7, 3353	4.9	11
107	Direct measurement of the bulk spin structure of noncentrosymmetric BiTeCl. <i>Physical Review B</i> , 2015 , 91,	3.3	11
106	Transport and magnetic properties of Fe/GaAs Schottky junctions for spin polarimetry applications. <i>Journal of Applied Physics</i> , 2011 , 109, 113708	2.5	11
105	Composition and morphology of fluorinated anodic oxides on InAs (1 1 1)A surface. <i>Applied Surface Science</i> , 2010 , 256, 5722-5726	6.7	11
104	Evolution of interface excitations under phase transition in two-dimensional layer of Cs on GaAs(1 0 0) and (1 1 1). <i>Applied Surface Science</i> , 2001 , 175-176, 175-180	6.7	11
103	Photoelectron spin polarization in the Bi ₂ Te ₃ (0001) topological insulator: Initial- and final-state effects in the photoemission process. <i>Physical Review B</i> , 2016 , 93,	3.3	10
102	Crystalline structure and magnetic properties of structurally ordered cobalt-iron alloys grown on Bi-containing topological insulators and systems with giant Rashba splitting. <i>CrystEngComm</i> , 2018 , 20, 3419-3427	3.3	10
101	Early Stages of Halogen Adsorption on Cation-Rich InAs(001): Surface Etching Mechanism. <i>Journal of Physical Chemistry C</i> , 2014 , 118, 10097-10105	3.8	10
100	The gigantic Rashba effect of surface states energetically buried in the topological insulator Bi ₂ Te ₂ Se. <i>New Journal of Physics</i> , 2014 , 16, 065016	2.9	10
99	Circular dichroism and superdiffusive transport at the surface of BiTeI. <i>Physical Review Letters</i> , 2013 , 111, 126603	7.4	10
98	Etching or Stabilization of GaAs(001) under Alkali and Halogen Adsorption. <i>Journal of Physical Chemistry C</i> , 2012 , 116, 8535-8540	3.8	10
97	Composition and structure of chemically prepared GaAs(1 1 1)A and (1 1 1)B surfaces. <i>Surface Science</i> , 2006 , 600, 577-582	1.8	10
96	Anomalously large gap and induced out-of-plane spin polarization in magnetically doped 2D Rashba system: V-doped BiTeI. <i>2D Materials</i> , 2017 , 4, 025055	5.9	9

95	Magnetic and Electronic Properties of Gd-Doped Topological Insulator Bi _{1.09} Gd _{0.06} Sb _{0.85} Te ₃ . <i>Journal of Experimental and Theoretical Physics</i> , 2019 , 129, 404-412	1	9
94	Role of anisotropy and spin-orbit interaction in the optical and dielectric properties of BiTeI and BiTeCl compounds. <i>JETP Letters</i> , 2015 , 101, 507-512	1.2	9
93	Superparamagnetism-induced mesoscopic electron focusing in topological insulators. <i>Physical Review B</i> , 2016 , 94,	3.3	9
92	Scattering properties of the three-dimensional topological insulator Sb ₂ Te ₃ : Coexistence of topologically trivial and nontrivial surface states with opposite spin-momentum helicity. <i>Physical Review B</i> , 2016 , 93,	3.3	9
91	Formation of anodic layers on InAs (111)III. Study of the chemical composition. <i>Semiconductors</i> , 2012 , 46, 552-558	0.7	9
90	Insulator-metal phase transitions of alkali atoms on GaAs(001). <i>Surface Science</i> , 2006 , 600, 287-297	1.8	9
89	Spin-resolved band structure of heterojunction Bi-bilayer/3D topological insulator in the quantum dimension regime in annealed BiTeSe. <i>Scientific Reports</i> , 2017 , 7, 45797	4.9	8
88	Dirac cone intensity asymmetry and surface magnetic field in V-doped and pristine topological insulators generated by synchrotron and laser radiation. <i>Scientific Reports</i> , 2018 , 8, 6544	4.9	8
87	Solar energy converters based on multi-junction photoemission solar cells. <i>Scientific Reports</i> , 2017 , 7, 16154	4.9	8
86	Quick ellipsometric technique for determining the thicknesses and optical constant profiles of Fe/SiO ₂ /Si(100) nanostructures during growth. <i>Technical Physics</i> , 2012 , 57, 1225-1229	0.5	8
85	Change in the electronic properties of an InAs (111)A surface at oxygen and fluorine adsorption. <i>Semiconductors</i> , 2012 , 46, 49-55	0.7	8
84	Cs-induced charge transfer on (2̄)-GaAs(001) studied by photoemission. <i>Physical Review B</i> , 2010 , 81,	3.3	8
83	Mapping the effect of defect-induced strain disorder on the Dirac states of topological insulators. <i>Physical Review B</i> , 2016 , 94,	3.3	8
82	Structural and vibrational properties of PVT grown BiTeCl microcrystals. <i>Materials Research Express</i> , 2019 , 6, 045912	1.7	8
81	Enhanced photovoltage on the surface of topological insulator via optical aging. <i>Applied Physics Letters</i> , 2018 , 112, 192104	3.4	8
80	Optical properties and electronic structure of BiTeCl and BiTeBr compounds. <i>Optics and Spectroscopy (English Translation of Optika i Spektroskopiya)</i> , 2016 , 121, 364-370	0.7	7
79	Energetic and Spatial Mapping of Resonant Electronic Excitations. <i>Journal of Physical Chemistry C</i> , 2016 , 120, 13843-13849	3.8	7
78	Optical properties of BiTeI semiconductor with a strong Rashba spin-orbit interaction. <i>Optics and Spectroscopy (English Translation of Optika i Spektroskopiya)</i> , 2014 , 117, 764-768	0.7	7

77	Chlorine adsorption on the InAs (001) surface. <i>Semiconductors</i> , 2011 , 45, 21-29	0.7	7
76	Metallicity and disorder at the alkali-metal/GaAs(001) interface. <i>Physical Review B</i> , 2001 , 64,	3.3	7
75	Cs/GaAs(100) surface: Two-dimensional metal or Hubbard insulator?. <i>JETP Letters</i> , 1999 , 70, 550-555	1.2	7
74	Single Electron Gating of Topological Insulators. <i>Advanced Materials</i> , 2016 , 28, 10073-10078	2.4	7
73	Conductance oscillations and zero-bias anomaly in a single superconducting junction to a three-dimensional Bi ₂ Te ₃ topological insulator. <i>Europhysics Letters</i> , 2017 , 119, 57009	1.6	6
72	GaAs(111) A and B surfaces in hydrazine sulfide solutions: Extreme polarity dependence of surface adsorption processes. <i>Physical Review B</i> , 2009 , 80,	3.3	6
71	Structure and magneto-electric properties of Co-based ferromagnetic films grown on the Pb _{0.71} Sn _{0.29} Te crystalline topological insulator. <i>Materials Chemistry and Physics</i> , 2020 , 240, 122134	4.4	6
70	Origin of spin-polarized photocurrents in the topological surface states of Bi ₂ Se ₃ . <i>Physical Review B</i> , 2018 , 98,	3.3	6
69	Photoemission and Injection Properties of a Vacuum Photodiode with Two Negative-Electron-Affinity Semiconductor Electrodes. <i>Physical Review Applied</i> , 2017 , 8,	4.3	5
68	A Study of the Crystal Structure of Co ₄₀ Fe ₄₀ B ₂₀ Epitaxial Films on a Bi ₂ Te ₃ Topological Insulator. <i>Technical Physics Letters</i> , 2018 , 44, 184-186	0.7	5
67	Magnetic-impurity-induced modifications to ultrafast carrier dynamics in the ferromagnetic topological insulators Sb ₂ V _x Te ₃ . <i>New Journal of Physics</i> , 2019 , 21, 093006	2.9	5
66	Backward Reconstructions on GaAs(001) Surface Induced by Atomic Hydrogen Reactions: Surfactant-Assisted Low-Temperature Surface Ordering. <i>Journal of Physical Chemistry C</i> , 2013 , 117, 9723-9733	3.8	5
65	Geometric and electronic structure of the Cs-doped Bi ₂ Se ₃ (0001) surface. <i>Physical Review B</i> , 2017 , 95,	3.3	5
64	Ferromagnetic HfO ₂ /Si/GaAs interface for spin-polarimetry applications. <i>Applied Physics Letters</i> , 2015 , 107, 123506	3.4	5
63	Ab-initio study of new Ga-rich GaAs(001) surface (4 \times 4) reconstruction. <i>Surface Science</i> , 2013 , 615, 97-102	1.8	5
62	Electrical properties and deep traps spectra in AlGaN films with nitrogen and gallium polarities prepared by molecular beam epitaxy. <i>Physica B: Condensed Matter</i> , 2009 , 404, 4870-4872	2.8	5
61	Adsorption of halogen atom (F, Cl, I) on cation-rich GaAs(001) surface. <i>IOP Conference Series: Materials Science and Engineering</i> , 2011 , 23, 012015	0.4	5
60	New reconstruction-stoichiometry correlation for GaAs(001) surface treated by atomic hydrogen. <i>Applied Surface Science</i> , 2008 , 254, 8041-8045	6.7	5

59	Optical anisotropy induced by cesium adsorption on the As-rich c(2B) reconstruction of GaAs(001). <i>Physical Review B</i> , 2004 , 69,	3.3	5
58	Effect of adsorption of electronegative and electropositive elements on the surface optical anisotropy of GaAs(001). <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 2976-2981		5
57	Specific features of the electronic, spin, and atomic structures of a topological insulator Bi ₂ Te _{2.4} Se _{0.6} . <i>Physics of the Solid State</i> , 2016 , 58, 779-787	0.8	5
56	Shubnikov-de Haas oscillations in p and n-type topological insulator (Bi Sb)Te. <i>Journal of Physics Condensed Matter</i> , 2018 , 30, 265001	1.8	5
55	AlN/GaN heterostructures for normally-off transistors. <i>Semiconductors</i> , 2017 , 51, 379-386	0.7	4
54	Ultrafast dynamics of an unoccupied surface resonance state in Bi ₂ Te ₂ Se. <i>Physical Review B</i> , 2018 , 97,	3.3	4
53	Effect of fluorine on the electrical properties of anodic oxide/InAs(111)A interface. <i>Semiconductors</i> , 2014 , 48, 307-311	0.7	4
52	Energy threshold of Cs-induced chemisorption of oxygen on a GaAs(Cs, O) surface. <i>JETP Letters</i> , 2008 , 88, 520-523	1.2	4
51	Enhanced surface state protection and band gap in the topological insulator PbBi ₄ Te ₄ S ₃ . <i>Physical Review Materials</i> , 2018 , 2,	3.2	4
50	Field Effect and Spin-Valve Effect in the PbSnTe Topological Crystalline Insulator. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2020 , 56, 553-557	0.6	4
49	Modification of the Surface Properties of PbSnTe<In> Epitaxial Layers with Composition near Band Inversion. <i>Technical Physics</i> , 2019 , 64, 1704-1708	0.5	4
48	Electronic correlation determining correlated plasmons in Sb-doped Bi ₂ Se ₃ . <i>Physical Review B</i> , 2019 , 100,	3.3	3
47	Inverted Dirac-electron population for broadband lasing in a thermally activated p-type topological insulator. <i>Physical Review B</i> , 2019 , 99,	3.3	3
46	Gigantic 2D laser-induced photovoltaic effect in magnetically doped topological insulators for surface zero-bias spin-polarized current generation. <i>2D Materials</i> , 2018 , 5, 015015	5.9	3
45	Properties of methylammonium lead iodide perovskite single crystals. <i>Journal of Structural Chemistry</i> , 2017 , 58, 1567-1572	0.9	3
44	The Peculiarities of Halogens Adsorption on A ₃ B ₅ (001) Surface. <i>IOP Conference Series: Materials Science and Engineering</i> , 2015 , 77, 012002	0.4	3
43	Reconstruction dependence of the etching and passivation of the GaAs(001) surface. <i>JETP Letters</i> , 2010 , 91, 466-470	1.2	3
42	New Ga-enriched reconstructions on the GaAs(001) surface. <i>JETP Letters</i> , 2009 , 89, 185-190	1.2	3

41	Preparation of As-rich (2x4) III-As (001) surfaces by wet chemical treatment and vacuum annealing. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 264-267		3
40	Bulklike behavior of the optical anisotropy of cation-rich (001) surfaces of Ga _{1-x} In _x As alloys. <i>Physical Review B</i> , 2004 , 69,	3.3	3
39	Energy-Gap Opening Near the Dirac Point after the Deposition of Cobalt on the (0001) Surface of the Topological Insulator BiSbTeSe ₂ . <i>Semiconductors</i> , 2020 , 54, 1051-1055	0.7	3
38	Spectral detection of spin-polarized ultra low-energy electrons in semiconductor heterostructures. <i>Ultramicroscopy</i> , 2020 , 218, 113076	3.1	3
37	A new imaging concept in spin polarimetry based on the spin-filter effect. <i>Journal of Synchrotron Radiation</i> , 2021 , 28, 864-875	2.4	3
36	Growth of Bi ₂ Se ₃ /graphene heterostructures with the room temperature high carrier mobility. <i>Journal of Materials Science</i> , 2021 , 56, 9330-9343	4.3	3
35	Topological states induced by local structural modification of the polar BiTeI(0001) surface. <i>New Journal of Physics</i> , 2018 , 20, 063035	2.9	3
34	Surface Inductivity Dynamics in PbSnTe:In Films in the Vicinity of a Band Inversion. <i>Semiconductors</i> , 2019 , 53, 1182-1186	0.7	2
33	Origin of Degradation of the CaF ₂ /BaF ₂ Buffer Layers on Si(111). <i>Doklady Physics</i> , 2020 , 65, 15-17	0.8	2
32	Spin and electronic structure of the topological insulator Bi _{1.5} Sb _{0.5} Te _{1.8} Se _{1.2} . <i>Materials Chemistry and Physics</i> , 2018 , 207, 253-258	4.4	2
31	Bidirectional surface photovoltage on a topological insulator. <i>Physical Review B</i> , 2019 , 100,	3.3	2
30	Forming interface in Pd/Fe/GaAs/InGaAs structure for optical detector of free-electron spin. <i>Technical Physics Letters</i> , 2012 , 38, 12-16	0.7	2
29	Reversible superstructural transitions on the GaAs(001) surface under the selective effect of iodine and cesium. <i>JETP Letters</i> , 2008 , 87, 35-38	1.2	2
28	Non-monotonic variation of the Kramers point band gap with increasing magnetic doping in BiTeI. <i>Scientific Reports</i> , 2021 , 11, 23332	4.9	2
27	Electrochemically exfoliated thin BiSe films and van der Waals heterostructures BiSe/graphene. <i>Nanotechnology</i> , 2020 , 31, 125602	3.4	2
26	Profiling spin and orbital texture of a topological insulator in full momentum space. <i>Physical Review B</i> , 2021 , 103,	3.3	2
25	CH ₃ NH ₃ PbI ₃ crystal growth, structure and composition. <i>Journal of Physics: Conference Series</i> , 2018 , 1124, 041008	0.3	2
24	Anomalous Behavior of the Elastic and Optical Properties in Bi _{1.5} Sb _{0.5} Te _{1.8} Se _{1.2} Topological Insulator Induced by Point Defects. <i>Physica Status Solidi (B): Basic Research</i> , 2018 , 255, 1800264	1.3	2

23	Modulation of the Dirac Point Band Gap in the Antiferromagnetic Topological Insulator MnBi ₂ Te ₄ due to the Surface Potential Gradient Change. <i>Journal of Experimental and Theoretical Physics</i> , 2022 , 134, 103-111	1	2
22	Features of the Impurity-Photoconductivity Spectra of PbSnTe(In) Epitaxial Films with Temperature Changes. <i>Semiconductors</i> , 2019 , 53, 1272-1277	0.7	1
21	Landau Level Broadening in the Three-Dimensional Topological Insulator Sb ₂ Te ₃ . <i>Physica Status Solidi - Rapid Research Letters</i> , 2018 , 12, 1800112	2.5	1
20	Impact of Ultrathin Pb Films on the Topological Surface and Quantum-Well States of Bi ₂ Se ₃ and Sb ₂ Te ₃ Topological Insulators. <i>Journal of Experimental and Theoretical Physics</i> , 2018 , 126, 535-540	1	1
19	Study of the morphology and optical properties of anodic oxide layers on InAs (111)III. <i>Semiconductors</i> , 2013 , 47, 555-560	0.7	1
18	Preparation of Anion - Stabilized III-V Surfaces using Wet Treatments. <i>Siberian Russian Workshop and Tutorial on Electron Devices and Materials</i> , 2006 ,		1
17	Band gap opening in the BiSbTeSe ₂ topological surface state induced by ferromagnetic surface reordering. <i>Physical Review Materials</i> , 2021 , 5,	3.2	1
16	Electronic Structure of Magnetic Topological Insulators Mn(Bi _{1-x} Sb _x) ₂ Te ₄ with Various Concentration of Sb Atoms. <i>JETP Letters</i> , 2022 , 115, 286-291	1.2	1
15	Vapor growth of Bi ₂ Se ₃ and Bi ₂ O ₂ Se crystals on mica. <i>Materials Research Bulletin</i> , 2020 , 129, 110906	5.1	0
14	Sign-Alternating Photoconductivity in PbSnTe:In Films in the Space-Charge-Limited Current Regime. <i>Semiconductors</i> , 2020 , 54, 951-955	0.7	0
13	Optical Phonon Spectrum of the Ge ₂ Sb ₂ Te ₅ Single Crystal. <i>JETP Letters</i> , 2021 , 113, 651-656	1.2	0
12	Photoemission Properties of a Multialkali Photocathode. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2021 , 57, 505-510	0.6	0
11	Preparation of Atomically Clean and Structurally Ordered Surfaces of Epitaxial CdTe Films for Subsequent Epitaxy. <i>Semiconductors</i> , 2021 , 55, S62-S66	0.7	0
10	Influence of quantizing magnetic field and Rashba effect on indium arsenide metal-oxide-semiconductor structure accumulation capacitance. <i>Journal of Applied Physics</i> , 2018 , 123, 173901	2.5	
9	Surfactant properties of cesium in molecular beam epitaxy of GaAs(100). <i>JETP Letters</i> , 2011 , 93, 585-590	1.2	
8	Origin of the broadening of surface optical transitions of As-rich and Ga-rich GaAs(0 0 1). <i>Surface Science</i> , 2003 , 529, 204-214	1.8	
7	Modulated photovoltage changes at the nonmetal-metal transition of the Na/GaAs(001) and K/GaAs(001) interfaces. <i>Surface Science</i> , 2001 , 488, 193-206	1.8	
6	Structural Characterization of Pb _{0.7} Sn _{0.3} Te Crystalline Topological Insulator Thin Films Grown on Si(111). <i>Semiconductors</i> , 2021 , 55, 682	0.7	

- 5 Features of MIS Structures Based on Insulating PbSnTe:In Films with the Composition in the Vicinity of the Band Inversion Related to Their Ferroelectric Properties. *Semiconductors*, **2020**, 54, 1325-1331 0.7
- 4 PHOTOEMISSION PROPERTIES OF THE MULTIALKALI PHOTOCATHODE. *Avtometriya*, **2021**, 57, 70-76 1.5
- 3 Change of the topological surface states induced by ferromagnetic metals deposited on BiSbTeSe₂. *Journal of Physics: Conference Series*, **2020**, 1697, 012095 0.3
- 2 Reversible superstructural transitions on the GaAs(001) surface under the selective effect of iodine and cesium **2010**, 87, 35
- 1 Optical and Transport Properties of Epitaxial Pb_{0.74}Sn_{0.26}Te(In) Films with a Modifiable Surface. *Semiconductors*, **2020**, 54, 1086-1091 0.7